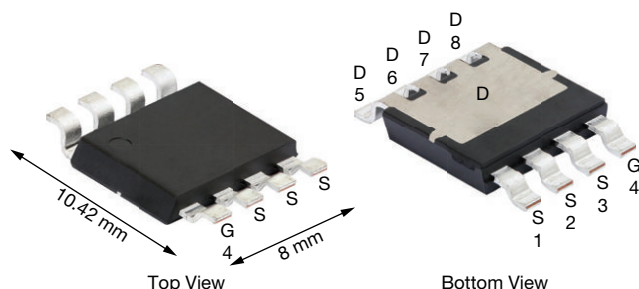


Automotive N-Channel 60 V (D-S) 175 °C MOSFET

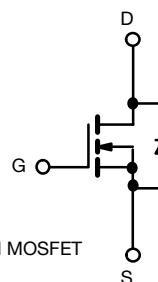
PowerPAK® 8 x 8LR


FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Thin 1.6 mm height
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE



N-Channel MOSFET

PRODUCT SUMMARY

V_{DS} (V)	60
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.00080
I_D (A) ^e	363
Configuration	Single

ORDERING INFORMATION

Package	PowerPAK 8 x 8LR
Lead (Pb)-free and halogen-free	SQJQ160ER (for detailed order number please see www.vishay.com/doc?79776)

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	60	V
Gate-source voltage	V_{GS}	± 20	
Continuous drain current ^e	I_D	363	A
		209	
Continuous source current (diode conduction)	I_S	194	
Pulsed drain current ^{a, e}	I_{DM}	802	
Single pulse avalanche current	I_{AS}	80	mJ
Single pulse avalanche energy	E_{AS}	320	
Maximum power dissipation ^e	P_D	214	W
		71	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^c		260	

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-ambient	R_{thJA}	44	°C/W
Junction-to-case (drain) ^d	R_{thJC}	0.7	

Notes

- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257)
- As per JESD51-14
- Values based on R_{thJC} and T_C of 25 °C- Actual values achievable will be dependent on the thermal characteristics of the complete system

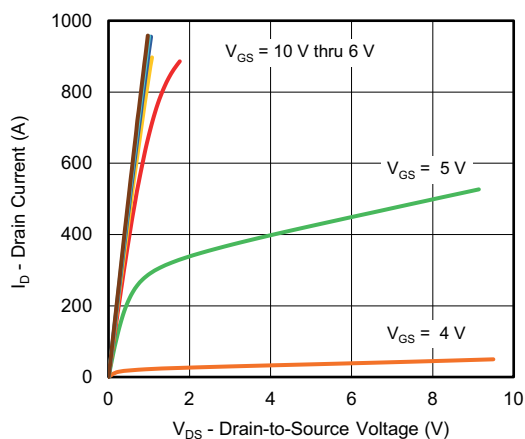
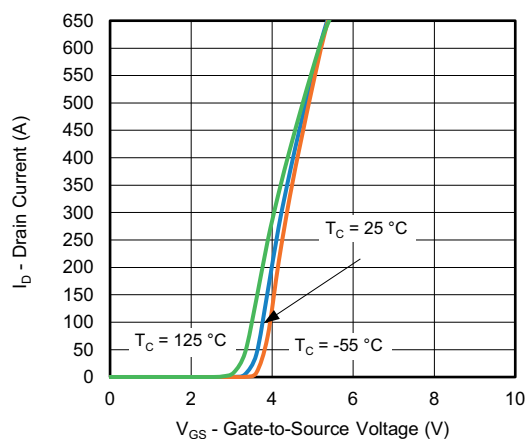
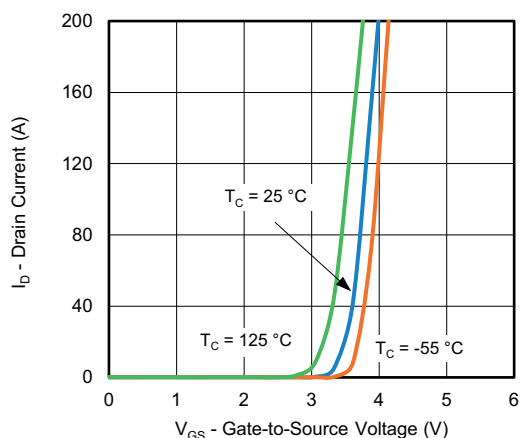
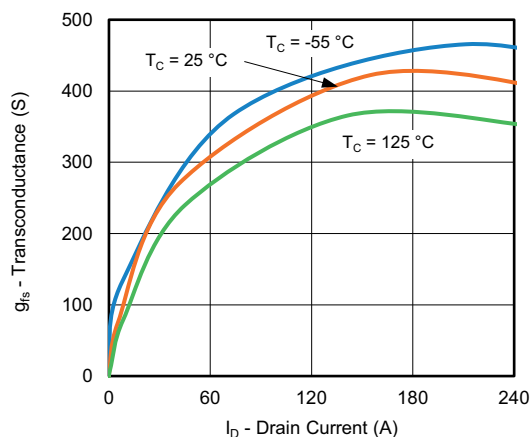
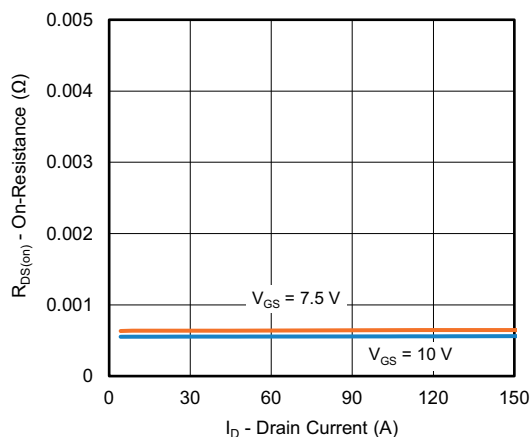
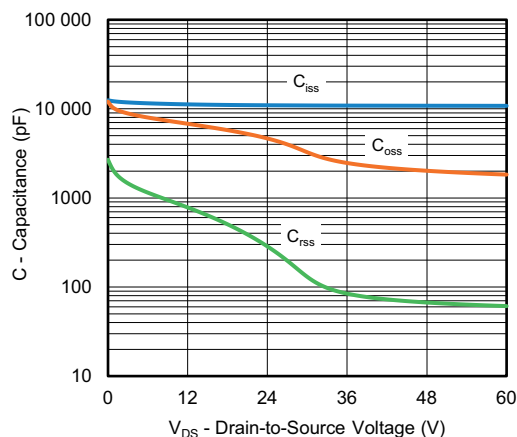


SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA		60	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2	2.8	3.5	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	500	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	50	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A	-	0.00056	0.00080	Ω
		V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.0014	
		V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0017	
Forward transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 40 A		-	220	-	S
Dynamic ^b							
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	10 944	15 322	pF
Output capacitance	C _{oss}			-	4486	6281	
Reverse transfer capacitance	C _{rss}			-	266	373	
Total gate charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 30 V, I _D = 50 A	-	169	254	nC
Gate-source charge ^c	Q _{gs}			-	48	-	
Gate-drain charge ^c	Q _{gd}			-	34	-	
Gate resistance	R _g	f = 1 MHz		0.4	1.6	3.2	Ω
Turn-on delay time ^c	t _{d(on)}	V _{DD} = 30 V, R _L = 0.6 Ω, I _D ≅ 50 A, V _{GEN} = 10 V, R _g = 1 Ω		-	20	30	ns
Rise time ^c	t _r			-	19	29	
Turn-off delay time ^c	t _{d(off)}			-	57	86	
Fall time ^c	t _f			-	18	27	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I _{SM}			-	-	802	A
Forward voltage	V _{SD}	I _F = 40 A, V _{GS} = 0 V		-	0.7	1.1	V
Body diode reverse recovery time	t _{rr}	I _F = 50 A, di/dt = 100 A/μs		-	86	172	ns
Body diode reverse recovery charge	Q _{rr}			-	154	308	nC
Reverse recovery fall time	t _a			-	49	-	ns
Reverse recovery rise time	t _b			-	34	-	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-3	-	A

Notes

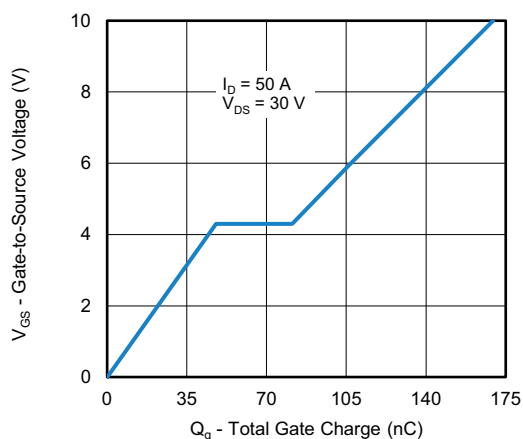
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

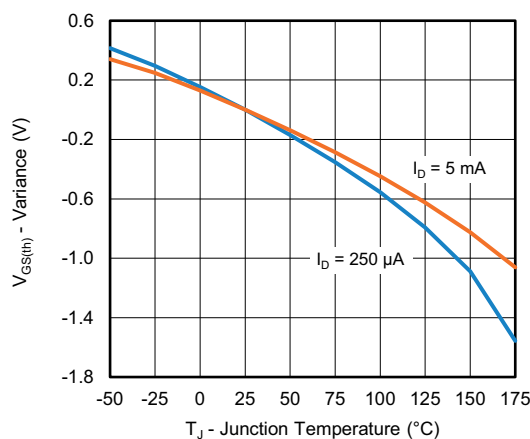
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance



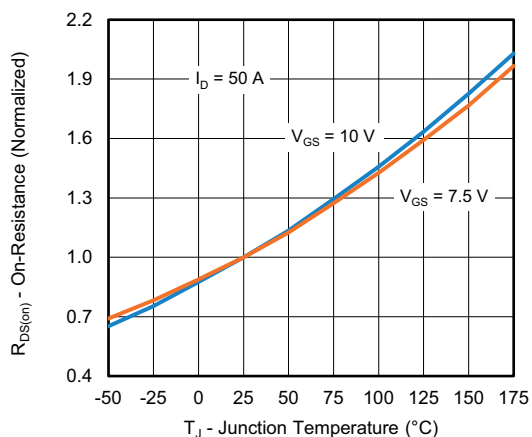
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



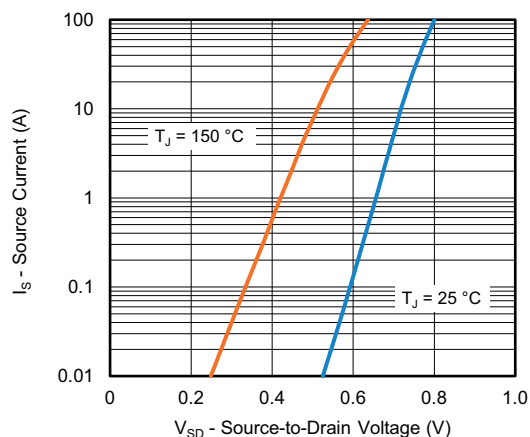
Gate Charge



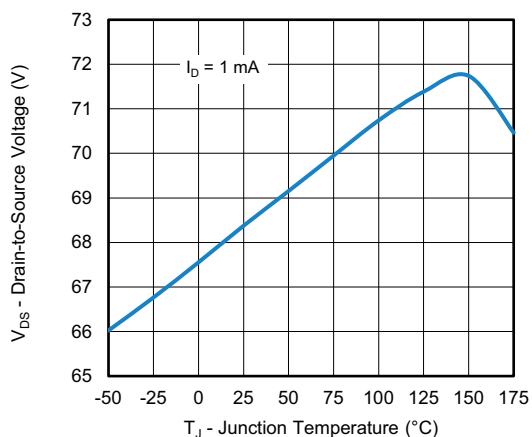
Threshold Voltage



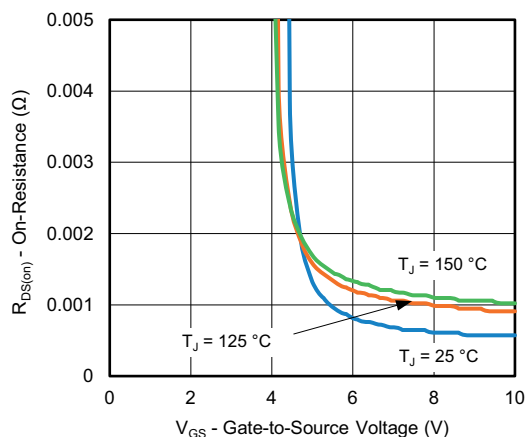
On-Resistance vs. Junction Temperature



Source Drain Diode Forward Voltage



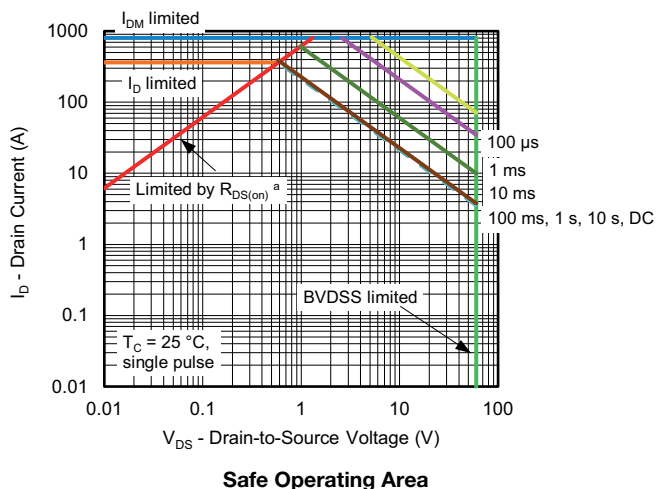
Drain Source Breakdown vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

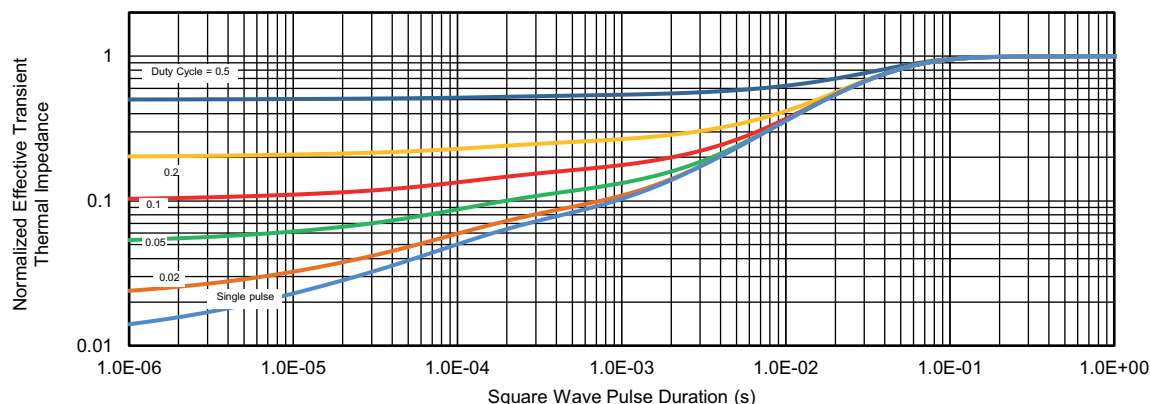


THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

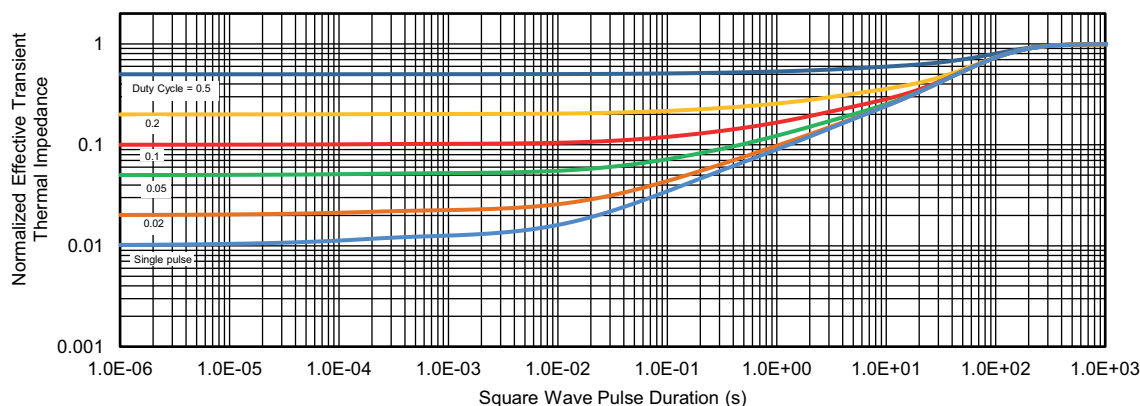


Note

- a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



Normalized Thermal Transient Impedance, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient



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